

Title (en)

SUBSTRATES FOR GROWING GROUP III NITRIDE CRYSTALS AND THEIR FABRICATION METHOD

Title (de)

SUBSTRATE ZUR ZÜCHTUNG VON GRUPPE-III-NITRID-KRISTALLEN UND DEREN HERSTELLUNGSVERFAHREN

Title (fr)

SUBSTRATS DE CROISSANCE DE CRISTAUX DE NITRURE DU GROUPE III ET LEUR PROCÉDÉ DE FABRICATION

Publication

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Application

EP 15767399 A 20150909

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Abstract (en)

[origin: WO2016040533A1] In one instance, the invention provides a substrate for growing a thick layer of group III nitride. The substrate has a first surface prepared for epitaxial growth of group III nitride and a second surface, opposite to the first surface, having a plurality of grooves. The invention also provides a method of producing a thick layer or a bulk crystal of group III nitride using a grooved substrate. The grooved substrate in one configuration grows a thick layer or a bulk crystal of group III nitride with reduced bow and/or spontaneous separation from the substrate.

IPC 8 full level

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